



DMN3061SWQ

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
0.01/	60mΩ @ VGS = 10V	2.7A
30V	100mΩ @ V _{GS} = 4.5V	2.1A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDs(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- DC-DC Converters
- Analog Switch

N-CHANNEL ENHANCEMENT MODE MOSFET

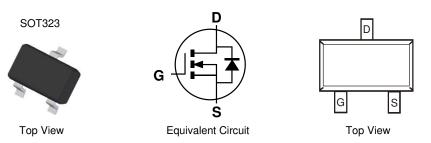
Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN3061SWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/guality/product-definitions/

Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.027 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3061SWQ-7	SOT323	3,000/Tape & Reel
DMN3061SWQ-13	SOT323	10,000/Tape & Reel

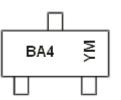
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\begin{array}{l} \mathsf{BA4}=\mathsf{Product} \ \mathsf{Type} \ \mathsf{Marking} \ \mathsf{Code} \\ \mathsf{YM} \ \mathsf{or} \ \overline{\mathsf{YM}}=\mathsf{Date} \ \mathsf{Code} \ \mathsf{Marking} \\ \mathsf{Y} \ \mathsf{or} \ \overline{\mathsf{Y}}=\mathsf{Year} \ (\mathsf{ex:} \ \mathsf{H}=2020) \\ \mathsf{M}=\mathsf{Month} \ (\mathsf{ex:} \ 9=\mathsf{September}) \end{array}$

Date Code Key

Notes:

Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	G	Н	I	J	K	L	М	N	0	Р	R	S
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	30	V		
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	D	2.7 2.2	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%		IDM	22	А	
Maximum Body Diode Forward Current (Note 5)			ls	0.67	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.49	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Rəja	254	°C/W
Total Power Dissipation (Note 6)	·	PD	0.65	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	191	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	1 2	1				
Drain-Source Breakdown Voltage	BV _{DSS}	30			V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current $@T_C = +25^{\circ}C$	C IDSS	_	_	1.0	μA	$V_{DS} = 24V, V_{GS} = 0V$
Gate-Source Leakage	IGSS			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	VGS(TH)	0.5		1.8	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
			41	60		$V_{GS} = 10V, I_{D} = 3.1A$
Static Drain-Source On-Resistance	RDS(ON)	—	48	100	mΩ	$V_{GS} = 4.5V, I_D = 2A$
			56	200		$V_{GS} = 3.3V, I_D = 1.5A$
Diode Forward Voltage	V _{SD}		0.7	1	V	$V_{GS} = 0V, I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		278	_	pF	
Output Capacitance	Coss	—	44	—	pF	└ V _{DS} = 15V, V _{GS} = 0V, └ f = 1.0MHz
Reverse Transfer Capacitance	Crss		29	—	pF	
Gate Resistance	Rg		4.2	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	Qg	_	3.5	—	nC	
Gate-Source Charge	Qgs	_	0.1	—	nC	V _{DS} = 15V, V _{GS} = 4.5V, I _D = 3A
Gate-Drain Charge	Q _{gd}	_	1.3	_	nC	
Turn-On Delay Time	td(on)	_	5.7	_	ns	
Turn-On Rise Time	t _R	_	97	_	ns	$V_{GS} = 10V, V_{DS} = 15V,$
Turn-Off Delay Time	td(OFF)	_	12.6	_	ns	$R_G = 3\Omega, R_L = 1.7\Omega$
Turn-Off Fall Time	tF	_	51	_	ns	

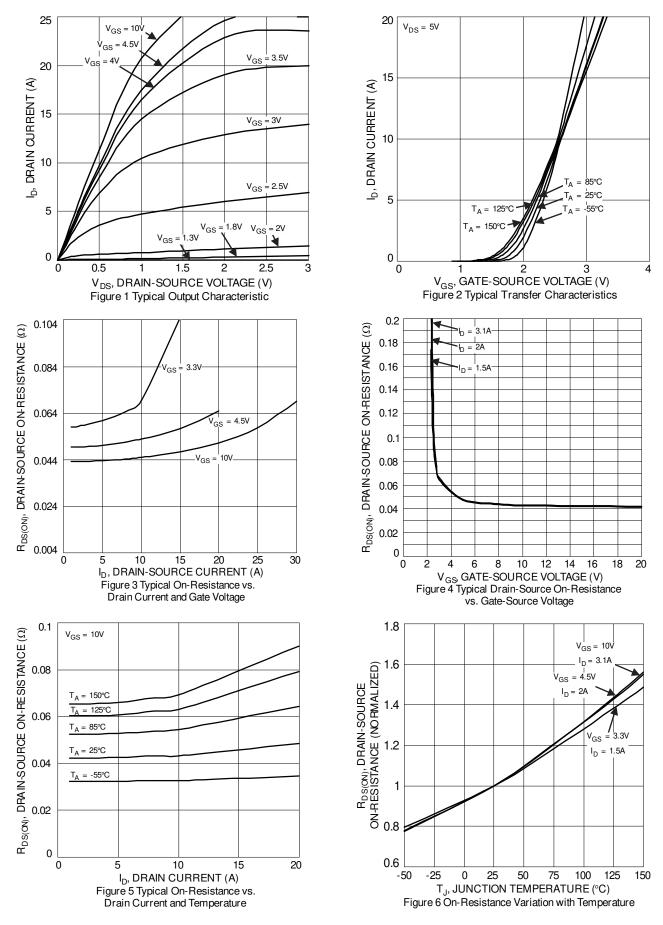
Notes:

Device mounted on FR-4 substrate PC board, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

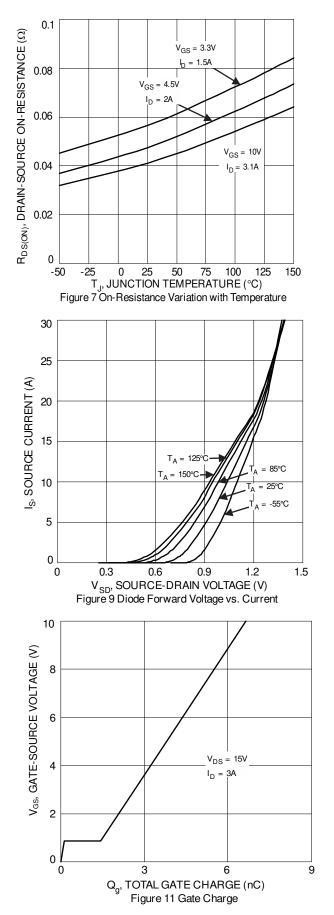


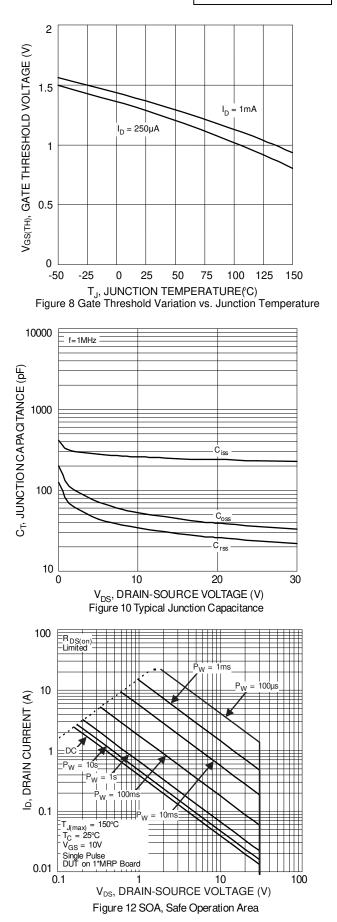
DMN3061SWQ



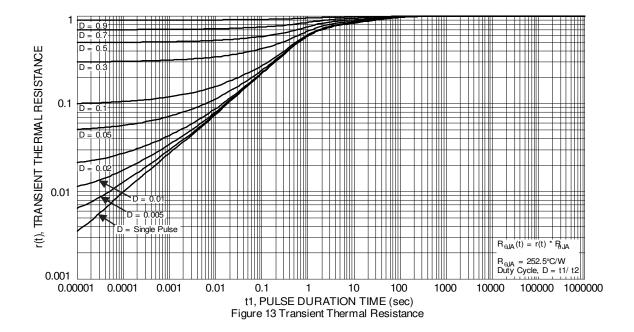


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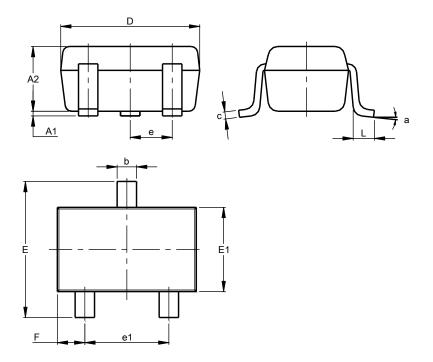




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

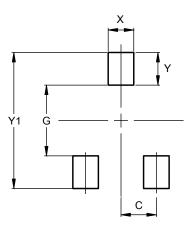
SOT323



SOT323								
Dim	Min	Max	Тур					
A1	0.00	0.10	0.05					
A2	0.90	1.00	0.95					
b	0.25	0.40	0.30					
С	0.10	0.18	0.11					
D	1.80	2.20	2.15					
Е	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	C).650 B	SC					
e1	1.20	1.40	1.30					
F	0.375	0.475	0.425					
L	0.25	0.40	0.30					
а	0°	8°						
All	Dimen	sions i	in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT323

Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
Y1	2.500



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